FOD819 4-Pin DIP High Speed Phototransistor Optocouplers

Description

The FOD819 consists of a gallium arsenide (GaAs) infra— red emitting diode, driving a high speed photo detector with integrated base—to—emitter resistor, R_{BE} , in a 4—pin dual—in—line package. It is designed to be an improved replacement to the popular FOD817 Series when higher speed performance is required in isolated data signal transmission.

Features

- High Speed Performance ~ 30 kHz
- Current Transfer Ratio: 100% to 600%
- Minimum BV_{CEO} of 80 V Guaranteed
- Safety and Regulatory Approvals:
- UL1577, 5,000 VAC_{RMS} for 1 Minute
- DIN EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Typical Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver



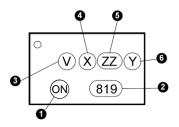
ON Semiconductor®

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DIP 4 PINS

MARKING DIAGRAM



1. ON = Company Logo

2. 819 = Device Number

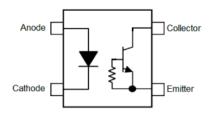
3. V = DIN EN/IEC60747-5-5 Option

4 X = One–Digit Year Code

5. ZZ = Digit Work Week

Y = Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

Safety and Insulation Ratings

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Table 1. SAFETY AND INSULATION RATINGS

Parameter		Characteristics
	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification		55/115/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Table 2.

Symbol	Parameter	Value	Unit
VPR	Input–to–Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10 \text{ s}$, Partial Discharge < 5 pC	1360	Vpeak
	Input–to–Output Test Voltage, Method B, $V_{IORM} x$ 1.875 = V_{PR} , 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC	1360	Vpeak
VIORM	Maximum Working Insulation Voltage	850	Vpeak
VIOTM	Highest Allowable Over–Voltage	8000	Vpeak
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option W, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature (Note 1)	175	°C
IS,INPUT	Input Current (Note 1)	400	mA
PS,OUTPUT	Output Power (Note 1)	700	mW
RIO	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ¹¹	Ω

^{1.} Safety limit values – maximum values allowed in the event of a failure.

Table 3. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
TOTAL PACKAGE			
T _{STG}	Storage Temperature	-55 to +125	°C
T _{OPR}	Operating Temperature	-55 to +110	°C
T _J	Junction Temperature	-55 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
θ _{JC}	Junction-to-Case Thermal Resistance	210	°C/W
P _{TOT}	Total Device Power Dissipation	200	mW
EMITTER			
IF	Continuous Forward Current	50	mA
V _R	Reverse Voltage	6	V
P _D	Power Dissipation	70	mW
טי	Derate Above 100°C	1.7	mW/°C

Table 3. ABSOLUTE MAXIMUM RATINGS (continued)

Symbol	Parameter	Value	Unit			
DETECTOR	DETECTOR					
V _{CEO}	Collector–Emitter Voltage	80	V			
V _{ECO}	Emitter–Collector Voltage	2	V			
I _C	Continuous Collector Current	30	mA			
P _C	Collector Power Dissipation	150	mW			
1.0	Derate Above 90°C	2.9	mW/°C			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

 $\textbf{Table 4. INDIVIDUAL COMPONENT CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ specified)$

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER	R			•	•	•
V _F	Forward Voltage	I _F = 1.5 mA		1.2	1.4	V
I _R	Reverse Current	V _R = 4.0 V			10	μΑ
Ct	Terminal Capacitance	V = 0, f = 1 kHz		30		pF
DETECT	OR					
I _{CEO}	Collector Dark Current	V _{CE} = 40 V, I _F = 0			100	nA
BV _{CEO}	Collector–Emitter Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_F = 0$	80	150		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_F = 0$	2	7		V
DC TRAN	ISFER CHARACTERISTICS					
CTR	Current Transfer Ratio (Note 2)	$I_F = 1.5 \text{ mA}, V_{CE} = 5 \text{ V}$	100		600	%
V _{CE(SAT)}	Saturation Voltage	$I_F = 1.5 \text{ mA}, I_C = 0.2 \text{ mA}$			0.3	V
I _{C(OFF)}	OFF-state collector current	$V_F = 0.7 \text{ V}, V_{CE} = 40 \text{ V}$			10	μΑ
AC TRAN	ISFER CHARACTERISTICS					
t _R	Rise Time (Saturated)	I_F = 1.5 mA, V_{CC} = 5 V, R_L = 10 k Ω		12		μs
t _F	Fall Time (Saturated)	(Note 3)		20		μs
t _{PHL}	Propagation Delay Time High-to-Low	I_F = 1.5 mA, V_{CC} = 5 V, R_L = 10 k Ω		9	30	μs
t _{PLH}	Propagation Delay Time Low-to-High	(Note 3)		18	30	μs

Current Transfer Ratio (CTR) = I_C / I_F x 100%.
Refer to test circuit setup.

Table 5. ISOLATION CHARACTERISTICS ($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage (Note 4)	$f = 60$ Hz, $t = 1$ minutes, $I_{I-O} \le 2 \mu A$	5000			VAC _{RMS}
R _{ISO}	Isolation Resistance	$V_{I-O} = 500 V_{DC}$		1 x 10 ¹¹		Ω
C _{ISO}	Isolation Capacitance	$V_{I-O} = 0$, $f = 1 \text{ MHz}$		0.6	1.0	pf

^{4.} For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

Typical Performance Curves

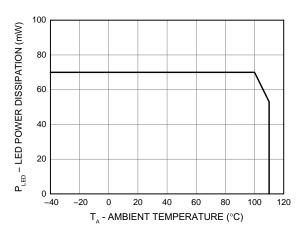


Figure 1. LED Power Dissipation vs. Ambient Temperature

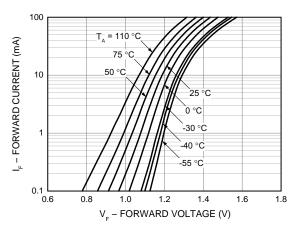


Figure 3. Forward Current vs. Forward Voltage

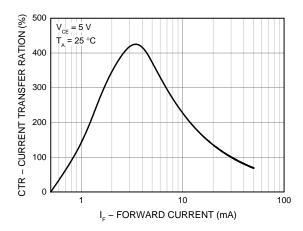


Figure 5. Current Transfer Ratio vs. Forward Current

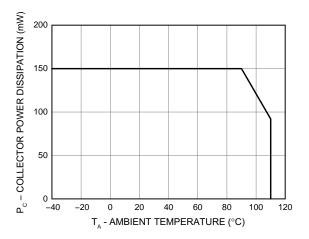


Figure 2. Collector Power Dissipation vs. Ambient Temperature

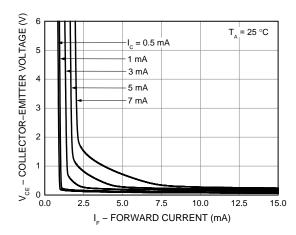


Figure 4. Collector-Emitter Voltage vs. Forward Current

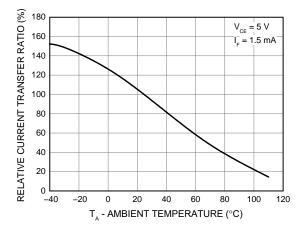


Figure 6. Relative Current Transfer Ratio vs. Ambient Temperature

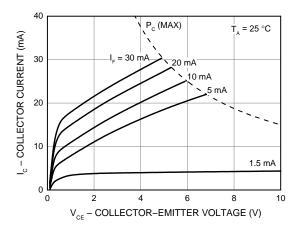


Figure 7. Collector Current vs. Collector-Emitter Voltage

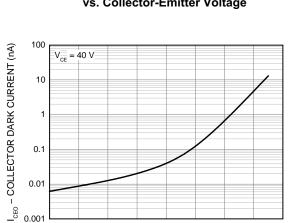


Figure 9. Collector Dark Current vs. Ambient Temperature

T_A - AMBIENT TEMPERATURE (°C)

0

20

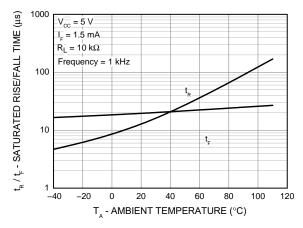


Figure 11. Saturated Rise / Fall Time vs. Ambient Temperature

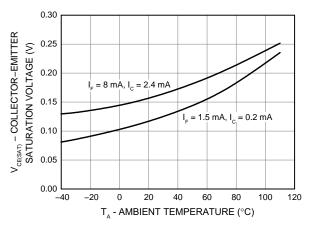


Figure 8. Collector-Emitter Saturation Voltage vs. Ambient Temperature

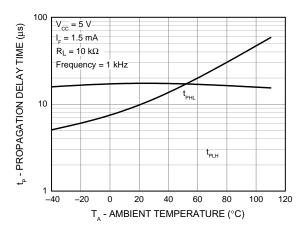


Figure 10. Propagation Delay vs. Ambient Temperature

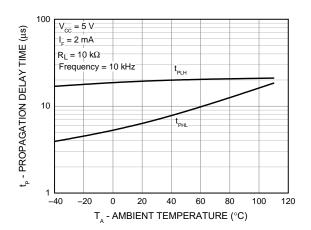


Figure 12. Propagation Delay vs. Ambient Temperature

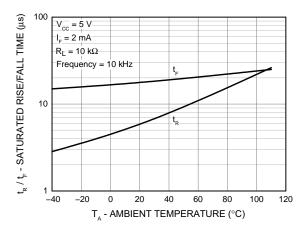


Figure 13. Collector Dark Current vs. Ambient Temperature

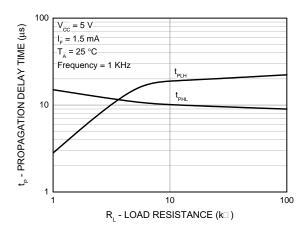


Figure 14. Propagation Delay vs. Ambient Temperature

Test Circuit

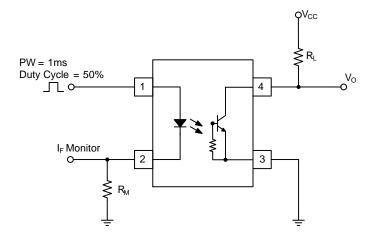


Figure 15. Test Circuit for Response Time

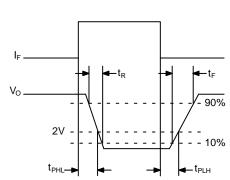


Figure 16. Timing Diagram

Reflow Profile

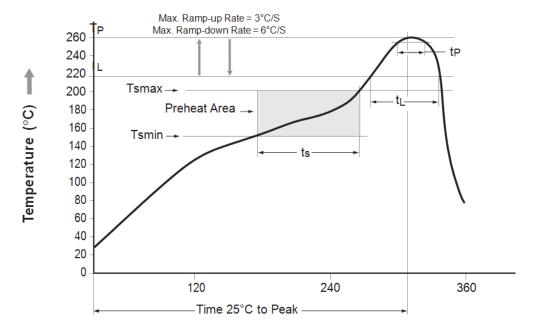


Figure 17. Reflow Profile

Table 6.

Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C / second max.
Time 25°C to Peak Temperature	8 minutes max.

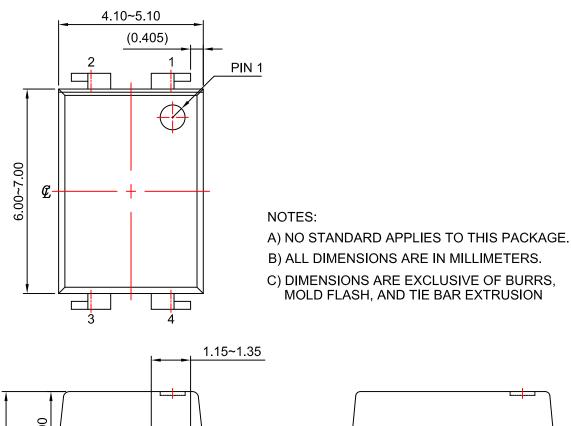
Table 7. ORDERING INFORMATION

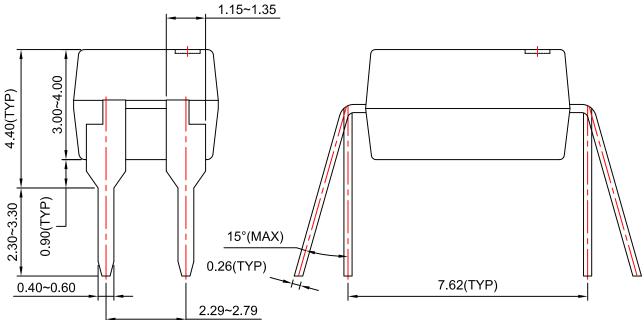
Part Number	Package	Packing Method †
FOD819	DIP 4–Pin	Tube (100 units per tube)
FOD819S	SMT 4-Pin (Lead Bend)	Tube (100 units per tube)
FOD819SD	SMT 4-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
FOD819300	DIP 4-Pin, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD8193S	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD8193SD	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tape and Reel (1,000 units per reel)
FOD819300W	DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

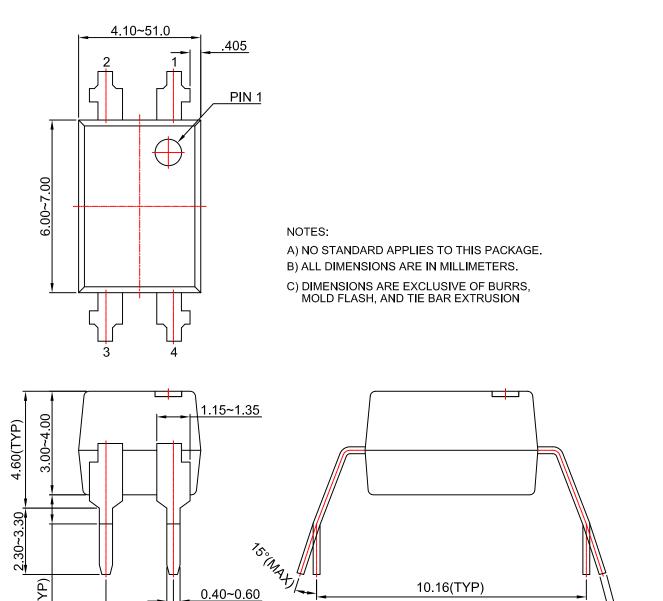
PACKAGE DIMENSIONS

PDIP4 4.6 x 6.5, 2.54P CASE 646CD ISSUE O





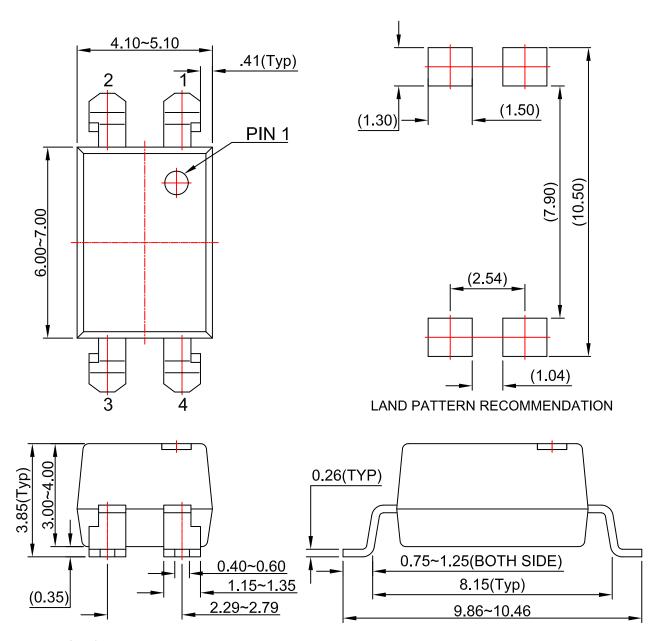
PDIP4 4.6 x 6.5, 2.54P CASE 646CA ISSUE O



.26(TYP)

2.29~2.79

PDIP4 GW CASE 709AH ISSUE A



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION

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